

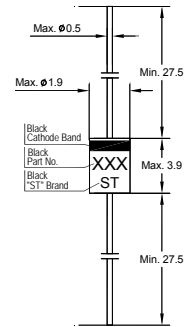
# 1SS171

## Silicon Epitaxial Planar Switching Diode

for high speed switching circuits

### Features

- High switching speed
- Small terminal capacitance
- Large forward current



Glass Case DO-35  
Dimensions in mm

### Absolute Maximum Ratings ( $T_a = 25\text{ }^\circ\text{C}$ )

Parameter	Symbol	Value	Unit
Repetitive Peak Reverse Voltage	$V_{RRM}$	80	V
Reverse Voltage	$V_R$	80	V
Average Forward Current	$I_{F(AV)}$	200	mA
Repetitive Peak Forward Current	$I_{FRM}$	600	mA
Non-Repetitive Peak Forward Surge Current (at $t = 1\text{ s}$ )	$I_{FSM}$	1	A
Junction Temperature	$T_j$	175	$^\circ\text{C}$
Storage Temperature Range	$T_{stg}$	- 65 to + 175	$^\circ\text{C}$

### Electrical Characteristics at $T_a = 25\text{ }^\circ\text{C}$

Parameter	Symbol	Max.	Unit
Forward Voltage at $I_F = 200\text{ mA}$	$V_F$	1.1	V
Reverse Current at $V_R = 15\text{ V}$ at $V_R = 75\text{ V}$	$I_R$	50 500	nA
Terminal Capacitance at $V_R = 0\text{ V}$ , $f = 1\text{ MHz}$	$C_T$	4	pF
Reverse Recovery Time at $I_F = 10\text{ mA}$ , $I_{rr} = 0.1\text{ I}_R$ , $R_L = 100\text{ }\Omega$	$t_{rr}$	20	ns

